NPN
TIP140
TIP141*
TIP142*
PNP
TIP145
TIP146*
TIP147*

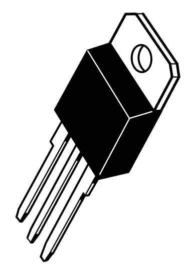
*Motorola Preferred Device

Darlington Complementary Silicon Power Transistors

. . . designed for general–purpose amplifier and low frequency switching applications.

- High DC Current Gain — Min h_{FE} = 1000 @ I_C = 5 A, V_{CE} = 4 V
- Collector–Emitter Sustaining Voltage — @ 30 mA
  $V_{CEO(sus)}$ = 60 Vdc (Min) — TIP140, TIP145
  80 Vdc (Min) — TIP141, TIP146
  100 Vdc (Min) — TIP142, TIP147
- Monolithic Construction with Built–In Base–Emitter Shunt Resistor

10 AMPERE DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 60–100 VOLTS 125 WATTS



CASE 340D–01

MAXIMUM RATINGS

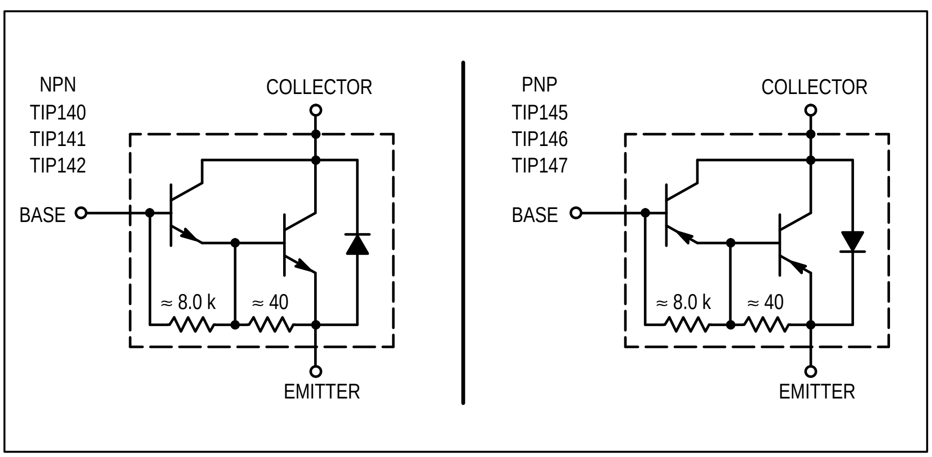
Rating	Symbol	TIP140 TIP145	TIP141 TIP146	TIP142 TIP147	Unit
Collector–Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector–Base Voltage	V_{CB}	60	80	100	Vdc
Emitter–Base Voltage	V_{EB}		5.0		Vdc
Collector Current — Continuous Peak (1)	I_C		10 15		Adc
Base Current — Continuous	I_B		0.5		Adc
Total Device Dissipation @ T_C = 25°C	P_D		125		Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}		–65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W
Thermal Resistance, Case to Ambient	$R_{\theta JA}$	35.7	°C/W

(1) 5 ms, ≤ 10% Duty Cycle.

DARLINGTON SCHEMATICS

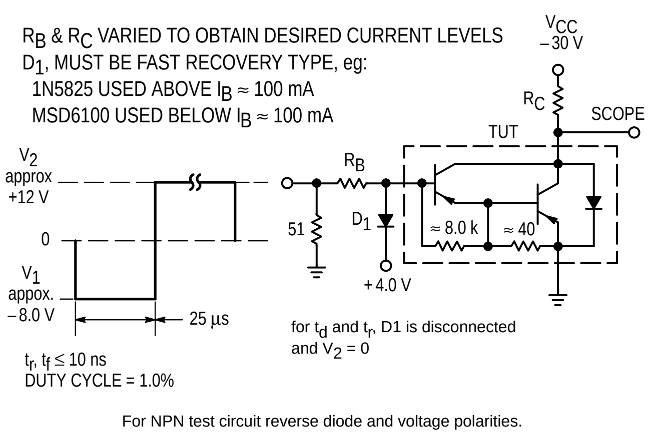


Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage (1)		$V_{CEO(sus)}$				Vdc
(I_C = 30 mA, I_B = 0)	TIP140, TIP145		60	—	—	
	TIP141, TIP146		80	—	—	
	TIP142, TIP147		100	—	—	
Collector Cutoff Current		I_{CEO}				mA
(V_{CE} = 30 Vdc, I_B = 0)	TIP140, TIP145		—	—	2.0	
(V_{CE} = 40 Vdc, I_B = 0)	TIP141, TIP146		—	—	2.0	
(V_{CE} = 50 Vdc, I_B = 0)	TIP142, TIP147		—	—	2.0	
Collector Cutoff Current		I_{CBO}				mA
(V_{CB} = 60 V, I_E = 0)	TIP140, TIP145		—	—	1.0	
(V_{CB} = 80 V, I_E = 0)	TIP141, TIP146		—	—	1.0	
(V_{CB} = 100 V, I_E = 0)	TIP142, TIP147		—	—	1.0	
Emitter Cutoff Current (V_{BE} = 5.0 V)		I_{EBO}	—	—	2 0	mA
ON CHARACTERISTICS (1)						
DC Current Gain		h_{FE}				—
(I_C = 5.0 A, V_{CE} = 4.0 V)			1000	—	—	
(I_C = 10 A, V_{CE} = 4.0 V)			500	—	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$				Vdc
(I_C = 5.0 A, I_B = 10 mA)			—	—	2.0	
(I_C = 10 A, I_B = 40 mA)			—	—	3.0	
Base–Emitter Saturation Voltage (I_C = 10 A, I_B = 40 mA)		$V_{BE(sat)}$	—	—	3.5	Vdc
Base–Emitter On Voltage (I_C = 10 A, V_{CE} = 4.0 Vdc)		$V_{BE(on)}$	—	—	3.0	Vdc
SWITCHING CHARACTERISTICS						
Resistive Load (See Figure 1)						
Delay Time	(V_{CC} = 30 V, I_C = 5.0 A, I_B = 20 mA, Duty Cycle ≤ 2.0%, I_{B1} = I_{B2}, R_C & R_B Varied, T_J = 25°C)	t_d	—	0.15	—	µs
Rise Time		t_r	—	0.55	—	µs
Storage Time		t_s	—	2.5	—	µs
Fall Time		t_f	—	2.5	—	µs

(1) Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%.



For NPN test circuit reverse diode and voltage polarities.

Figure 1. Switching Times Test Circuit

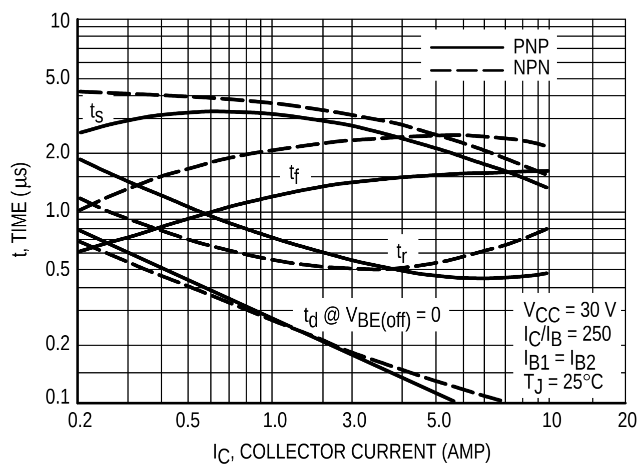


Figure 2. Switching Times

TYPICAL CHARACTERISTICS

NPN
TIP140, TIP141, TIP142

PNP
TIP145, TIP146, TIP147

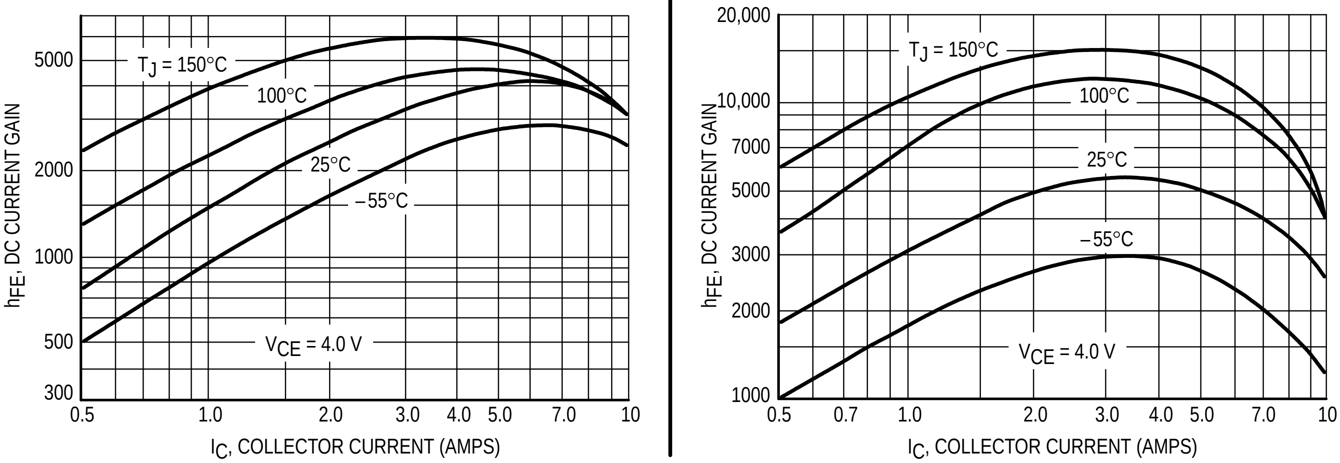


Figure 3. DC Current Gain versus Collector Current

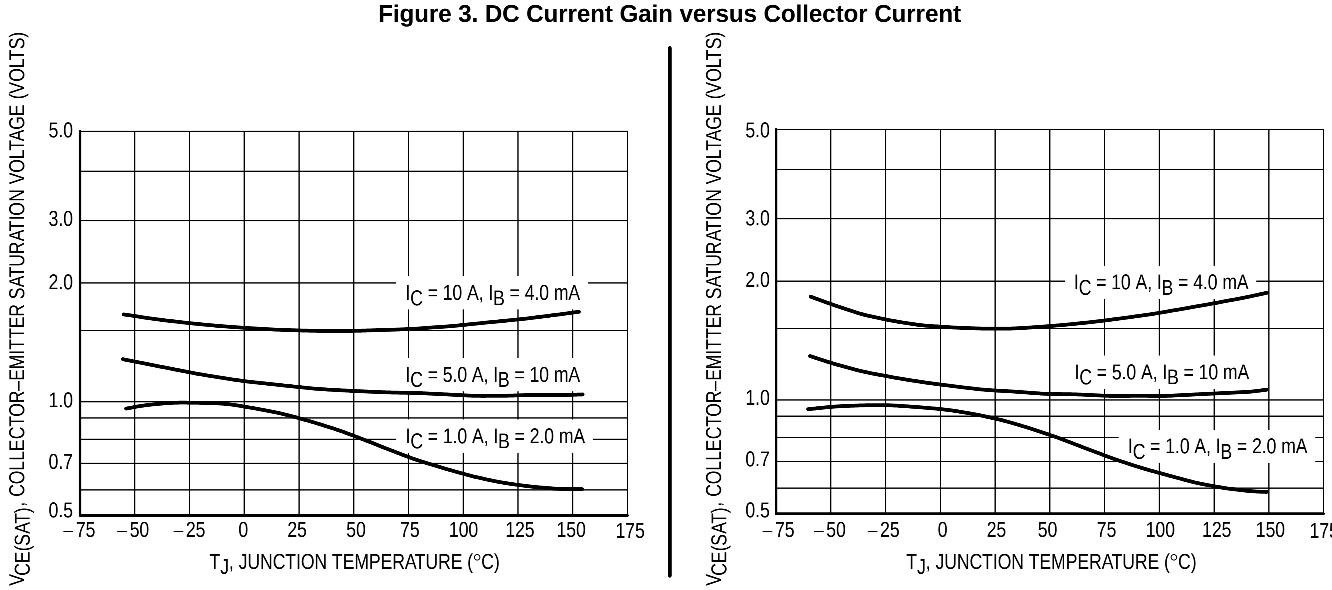


Figure 4. Collector−Emitter Saturation Voltage

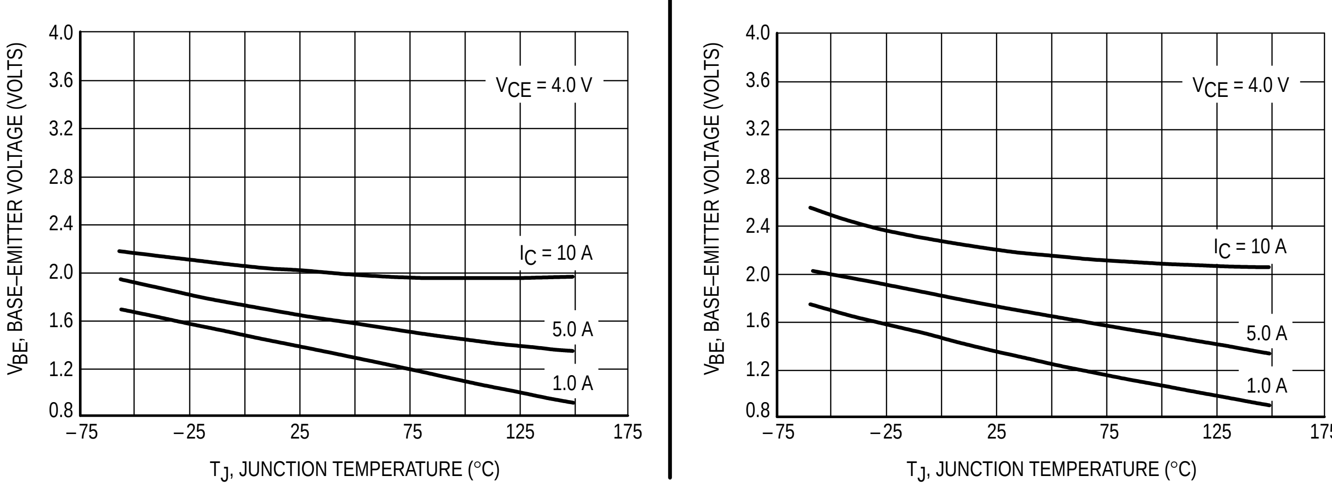


Figure 5. Base−Emitter Voltage

ACTIVE–REGION SAFE OPERATING AREA

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

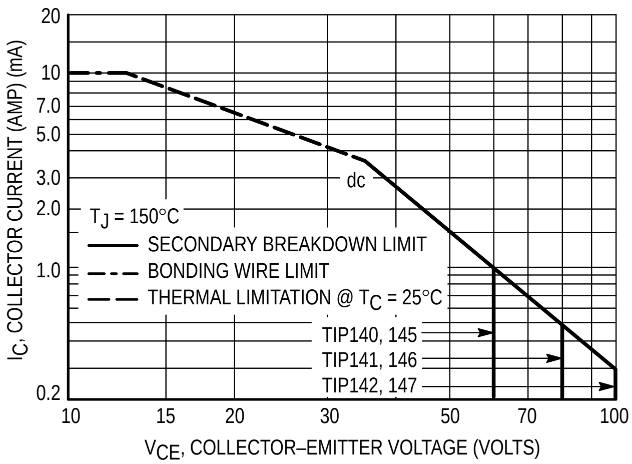


Figure 6. Active–Region Safe Operating Area

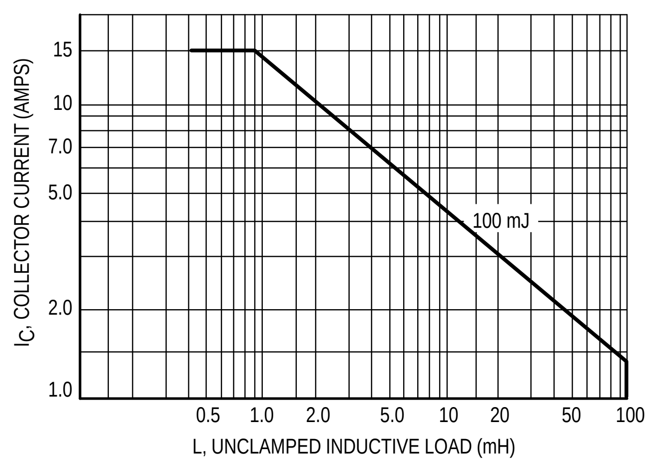
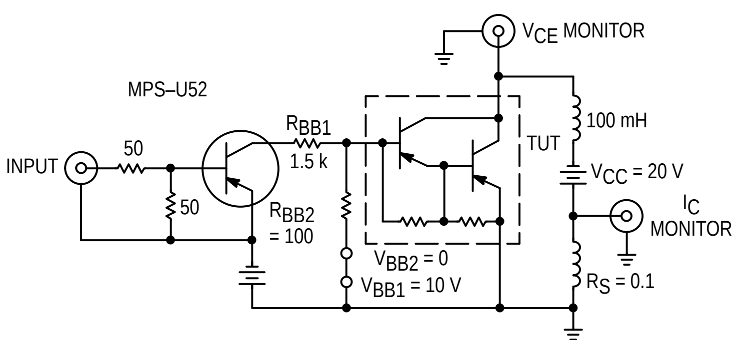
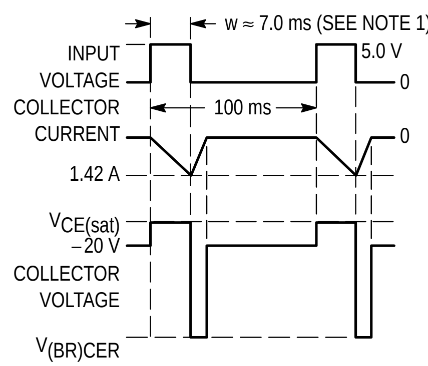


Figure 7. Unclamped Inductive Load



TEST CIRCUIT

NOTE 1: Input pulse width is increased until I_{CM} = 1.42 A.
NOTE 2: For NPN test circuit reverse polarities.



VOLTAGE AND CURRENT WAVEFORMS

Figure 8. Inductive Load

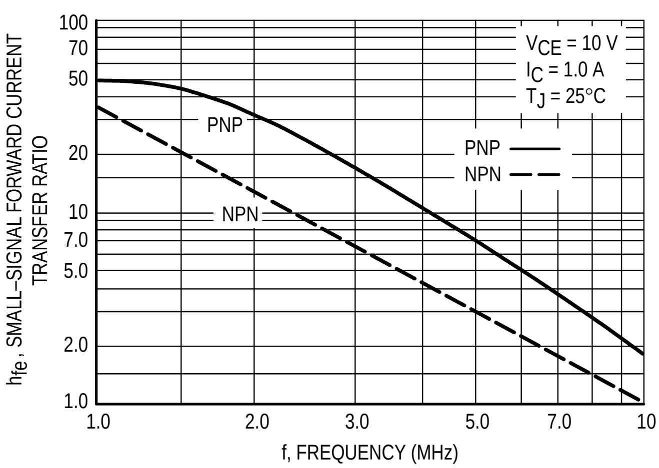


Figure 9. Magnitude of Common Emitter Small–Signal Short–Circuit Forward Current Transfer Ratio

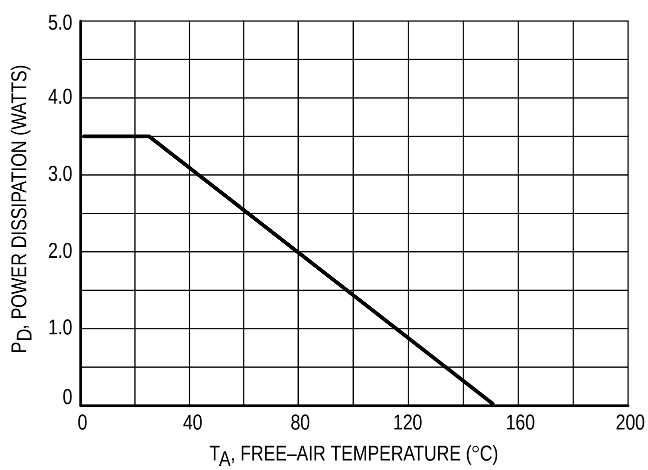
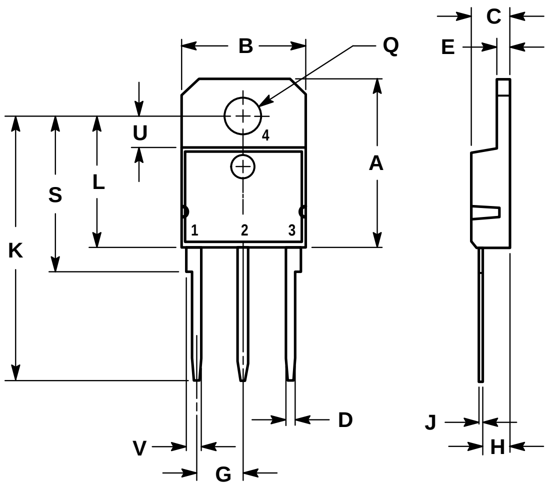


Figure 10. Free–Air Temperature Power Derating

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	19.00	19.60	0.749	0.771
B	14.00	14.50	0.551	0.570
C	4.20	4.70	0.165	0.185
D	1.00	1.30	0.040	0.051
E	1.45	1.65	0.058	0.064
G	5.21	5.72	0.206	0.225
H	2.60	3.00	0.103	0.118
J	0.40	0.60	0.016	0.023
K	28.50	32.00	1.123	1.259
L	14.70	15.30	0.579	0.602
Q	4.00	4.25	0.158	0.167
S	17.50	18.10	0.689	0.712
U	3.40	3.80	0.134	0.149
V	1.50	2.00	0.060	0.078

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 340D–01
TO–218AC
ISSUE A

How to reach us:
USA / EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609
INTERNET: http://Design–NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki,
6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298